Vishay Siliconix

N-Channel 20 V (D-S) MOSFET



PRODUCT SUMMARY						
V _{DS} (V)	20					
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.00135					
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5 \text{ V}$	0.00175					
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 2.5 \text{ V}$	0.00460					
Q _g typ. (nC)	18.2					
I _D (A)	177 ^g					
Configuration	Single					

FEATURES

- TrenchFET® Gen IV power MOSFET
- \bullet Optimized $Q_g,\ Q_{gd},\ and\ Q_{gd}/Q_{gs}$ ratio reduces switching related power loss

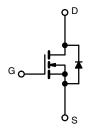
COMPLIANT HALOGEN **FREE**

100 % R_a and UIS tested

· Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

APPLICATIONS

- Synchronous rectification
- High power density DC/DC
- Synchronous buck converter
- · Load switching



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK SO-8
Lead (Pb)-free and halogen-free	SiR800ADP-T1-GE3

ABSOLUTE MAXIMUM RATING	iS (T _A = 25 °C, υ	nless other	wise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	20	V	
Gate-source voltage		V_{GS}	+12 / -8	7 v	
	T _C = 25 °C		177		
O. alia a sa daile a suad (T 450.00)	T _C = 70 °C		142		
Continuous drain current (T _J = 150 °C)	T _A = 25 °C	l _D	50.2 ^{b, c}		
	T _A = 70 °C	1	40.2 ^{b, c}		
Pulsed drain current (t = 100 μs)		I _{DM}	150	Α	
Continuous source drain diade surrent	T _C = 25 °C		56.8		
Continuous source-drain diode current	T _A = 25 °C	- I _S	4.5 ^{b, c}		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	20		
Single pulse avalanche energy L = 0.1 m		E _{AS}	20	mJ	
	T _C = 25 °C		62.5	\\\\	
NA	T _C = 70 °C		40		
Maximum power dissipation	T _A = 25 °C	P _D	5 b, c	W	
	T _A = 70 °C	İ	3.2 b, c	1	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	°C	
Soldering recommendations (peak temperature) c			260		

THERMAL RESISTANCE RATING	GS				
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^b	t ≤ 10 s	R _{thJA}	20	25	°C/W
Maximum junction-to-case (drain)	Steady state	R _{thJC}	1.7	2	C/VV

Notes

- a. Package limited
- Surface mounted on 1" x 1" FR4 board
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 70 °C/W
- $T_C = 25 \, ^{\circ}C$



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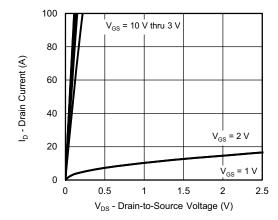
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static					•	•	
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20	-	-	V	
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	I _D = 10 mA	-	18	-		
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-3.6	-	mV/°C	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.6	-	1.5	V	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = +12 / -8 \text{ V}$	-	-	100	nA	
Zana and a self-anni davida a senset		V _{DS} = 20 V, V _{GS} = 0 V	-	-	1	μΑ	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V, T _J = 70 °C	-	-	15		
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	40	-	-	Α	
	, ,	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	-	0.00112	0.00135		
Drain-source on-state resistance ^a	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	0.00145	0.00175	Ω			
			-	0.00350	0.00460	1	
Forward transconductance a	9fs	$V_{DS} = 15 \text{ V}, I_D = 10 \text{ A}$	-	60	-	S	
Dynamic ^b					•		
Input capacitance	C _{iss}		-	3415	-		
Output capacitance	C _{oss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	1290	-	pF	
Reverse transfer capacitance	C _{rss}		-	72	-	۰,	
		$V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$	-	35.2	53		
Total gate charge	Q_g		-	18.2	27.5		
Gate-source charge	Q _{qs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$	-	7.3	-	nC	
Gate-drain charge			-	3.6	-		
Gate resistance	T - T	f = 1 MHz	0.4	0.85	1.4	Ω	
Turn-on delay time	t _{d(on)}		-	20	40		
Rise time		$V_{DD} = 10 \text{ V}, R_{I} = 1 \Omega, I_{D} \cong 10 \text{ A},$	-	13	26		
Turn-off delay time	t _{d(off)}		-	40	80		
Fall time	t _f		-	10	20		
Turn-on delay time	t _{d(on)}		-	12	24	ns	
Rise time	t _r	V_{DD} = 10 V, R_L = 1 Ω , $I_D \cong$ 10 A,	-	5	10		
Turn-off delay time	t _{d(off)}	$V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$	-	34	68		
Fall time	t _f		-	6			
Drain-Source Body Diode Characteristi	cs		1		•	ı	
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	56.8		
Pulse diode forward current	I _{SM}		-	-	150	Α	
Body diode voltage	V _{SD}	I _S = 5 A, V _{GS} = 0 V	-	0.73	1.1	V	
Body diode reverse recovery time	t _{rr}		-	32	64	ns	
Body diode reverse recovery charge	Q _{rr}	$I_F = 10 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	-	21	42	nC	
Reverse recovery fall time	t _a	$T_J = 25 ^{\circ}\text{C}$	-	16	-		
Reverse recovery rise time	t _b		-	16	-	ns	

Notes

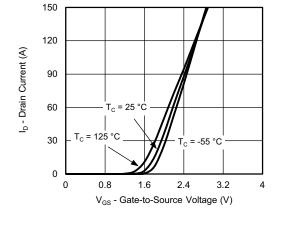
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

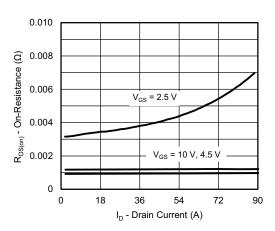




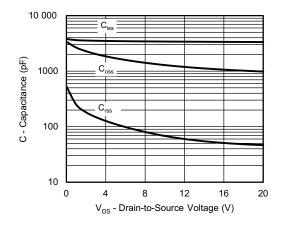
Output Characteristics



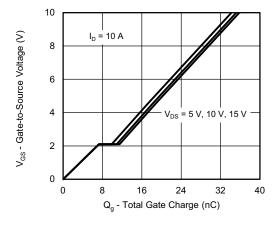
Transfer Characteristics



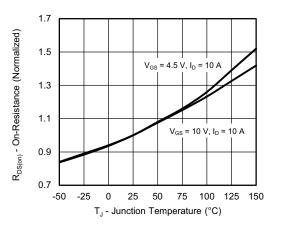
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

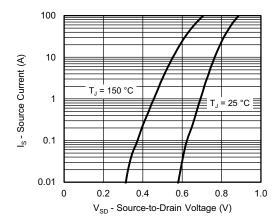


Gate Charge

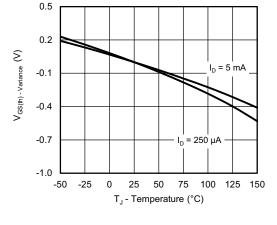


On-Resistance vs. Junction Temperature

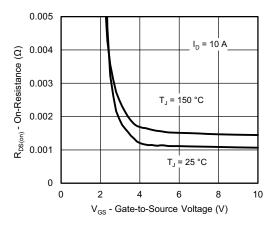




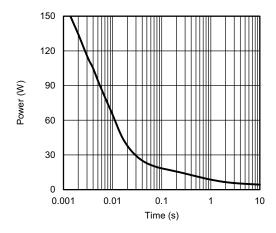
Source-Drain Diode Forward Voltage



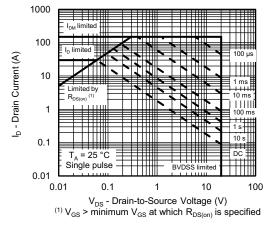
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage

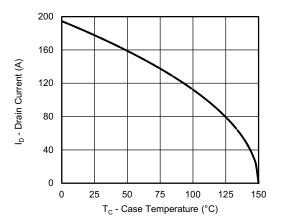


Single Pulse Power, Junction-to-Ambient

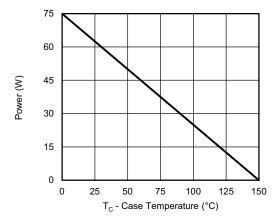


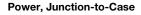
Safe Operating Area, Junction-to-Ambient

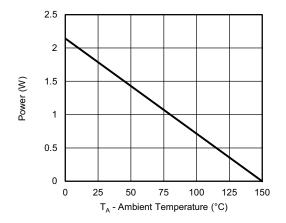




Current Derating a



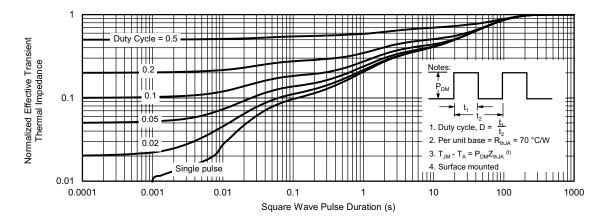




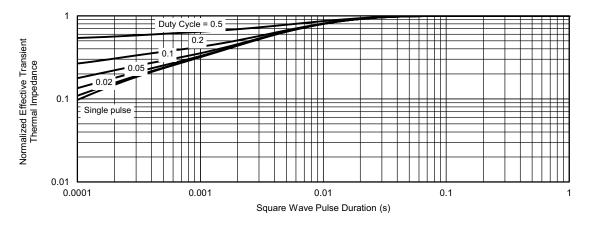
Power, Junction-to-Ambient

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?79335.



DWG: 5881

PowerPAK® SO-8, (Single/Dual)

Notes 1. Inch will govern. 2 Dimensions exclusive of mold gate burrs.

3. Dimensions exclusive of mold flash and cutting burrs.

Backside View of Dual Pad

DIM.		MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX		
Α	0.97	1.04	1.12	0.038	0.041	0.044		
A1		-	0.05	0	_	0.002		
b	0.33	0.41	0.51	0.013	0.016	0.020		
С	0.23	0.28	0.33	0.009	0.011	0.013		
D	5.05	5.15	5.26	0.199	0.203	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.56	3.76	3.91	0.140	0.148	0.154		
D3	1.32	1.50	1.68	0.052	0.059	0.066		
D4	0.57 typ. 0.0225 typ.				0.0225 typ.			
D5		3.98 typ.			0.157 typ.			
Е	6.05	6.15	6.25	0.238	0.242	0.246		
E1	5.79	5.89	5.99	0.228	0.232	0.236		
E2	3.48	3.66	3.84	0.137	0.144	0.151		
E3	3.68	3.78	3.91	0.145	0.149	0.154		
E4		0.75 typ.			0.030 typ.			
е		1.27 BSC		0.050 BSC				
K		1.27 typ.		0.050 typ.				
K1	0.56	-	-	0.022	-	-		
Н	0.51	0.61	0.71	0.020	0.024	0.028		
L	0.51	0.61	0.71	0.020	0.024	0.028		
L1	0.06	0.13	0.20	0.002	0.005	0.008		
θ	0°	-	12°	0°	-	12°		
W	0.15	0.25	0.36	0.006	0.010	0.014		
М		0.125 typ.			0.005 typ.			

Revison: 13-Feb-17 1 Document Number: 71655



RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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